

## **Method of Patterning a Magnetic Memory Cell Bottom Electrode Before Magnetic Stack Deposition**

### **ABSTRACT OF THE DISCLOSURE**

A method of patterning a bottom electrode for a magnetic memory cell. The bottom electrode is patterned prior to the deposition of the soft layer of the magnetic tunnel junction (MTJ) material stack, preventing the formation of fencing on the sidewalls of the soft layer, which can cause shorts to subsequently formed conductive lines of the magnetic memory device. A sacrificial mask is used to pattern the bottom electrode material, and at least a portion of the sacrificial mask is consumed or removed during the patterning of the bottom electrode material. The soft layer is then deposited and patterned using a hard mask.